



3LP02M — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- High-speed switching.
- 2.5V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-0.2	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-0.8	A
Allowable Power Dissipation	P _D		0.15	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-100μA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-100mA	0.21	0.3		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-100mA, V _{GS} =-4V		2.4	3.1	Ω
	R _{DS(on)2}	I _D =-50mA, V _{GS} =-2.5V		3.5	4.9	Ω
	R _{DS(on)3}	I _D =-10mA, V _{GS} =-1.5V		10	20	Ω
Input Capacitance	C _{iss}	V _{DS} =-10V, f=1MHz		28		pF
Output Capacitance	C _{oss}	V _{DS} =-10V, f=1MHz		15		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-10V, f=1MHz		5.2		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		24		ns
Rise Time	t _r	See specified Test Circuit.		75		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		200		ns
Fall Time	t _f	See specified Test Circuit.		150		ns

Marking : XD

Continued on next page.

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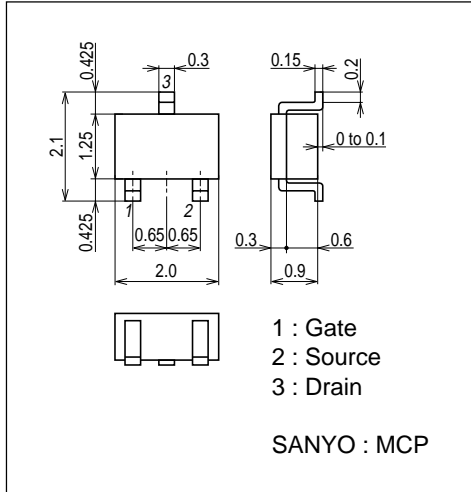
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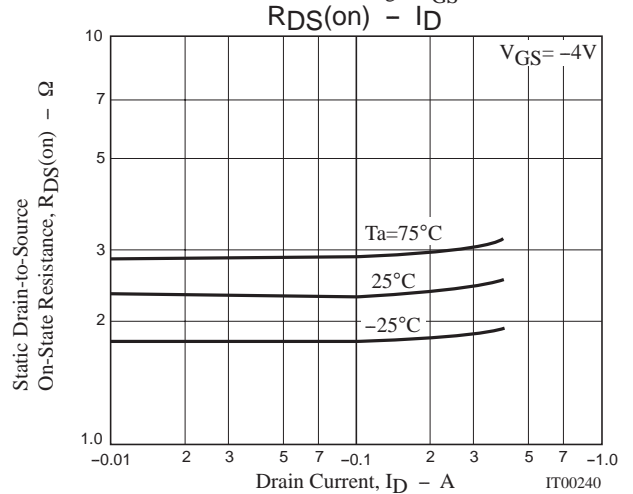
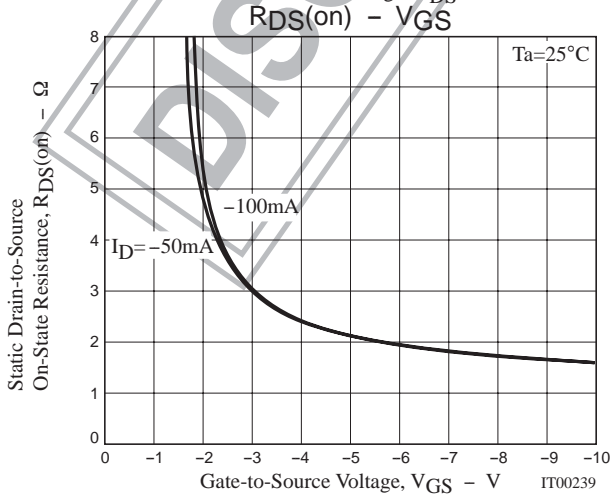
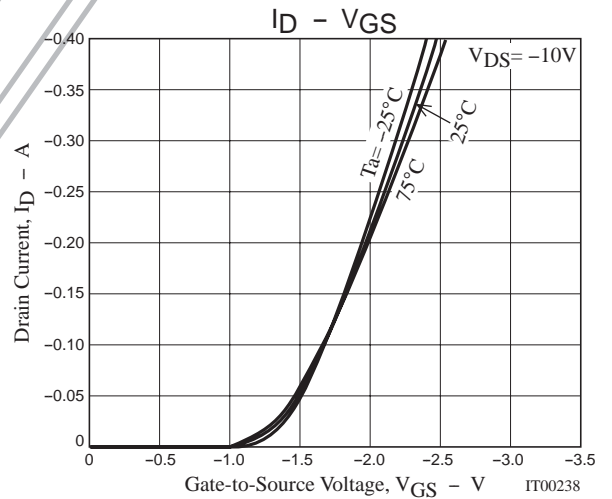
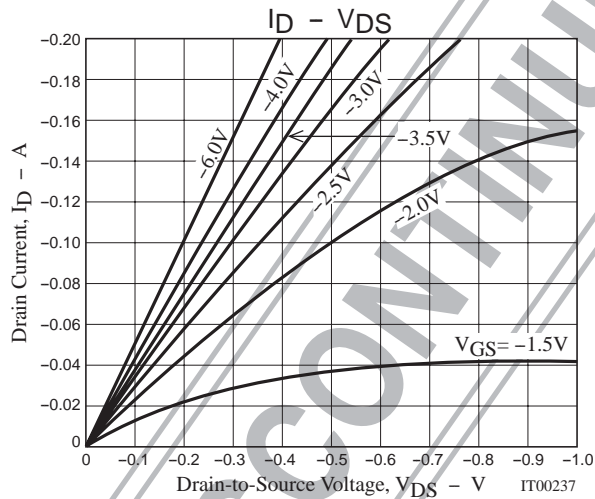
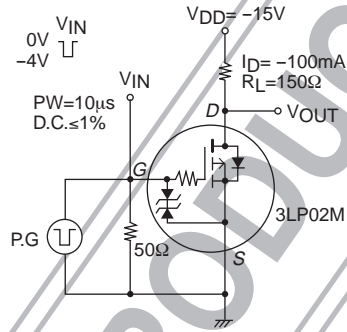
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	$V_{DS}=-10V, V_{GS}=-10V, I_D=-200mA$		2		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-10V, V_{GS}=-10V, I_D=-200mA$		0.25		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-10V, V_{GS}=-10V, I_D=-200mA$		0.35		nC
Diode Forward Voltage	VSD	$I_S=-200mA, V_{GS}=0V$		-0.82	-1.2	V

Package Dimensions

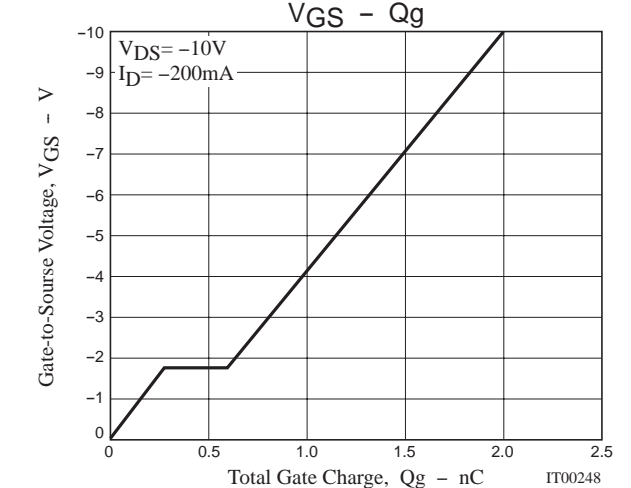
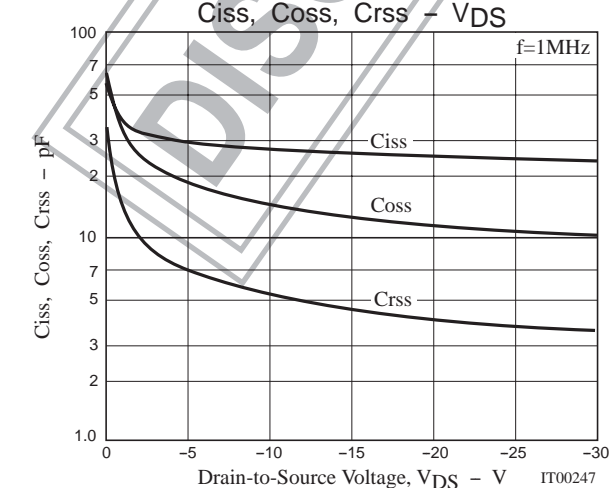
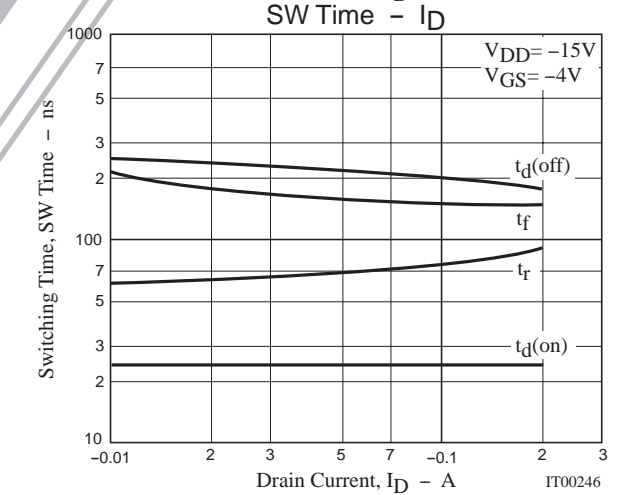
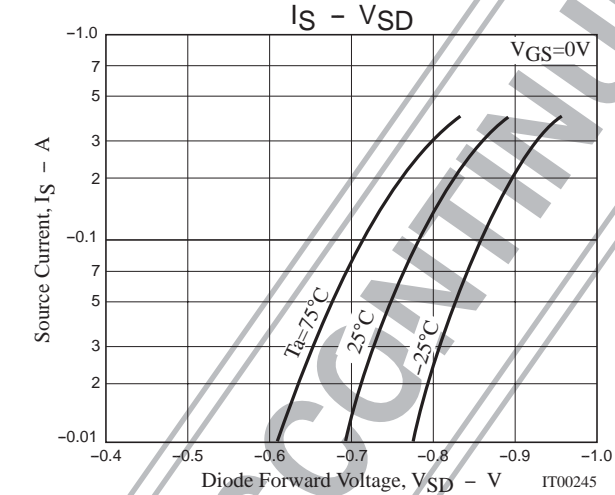
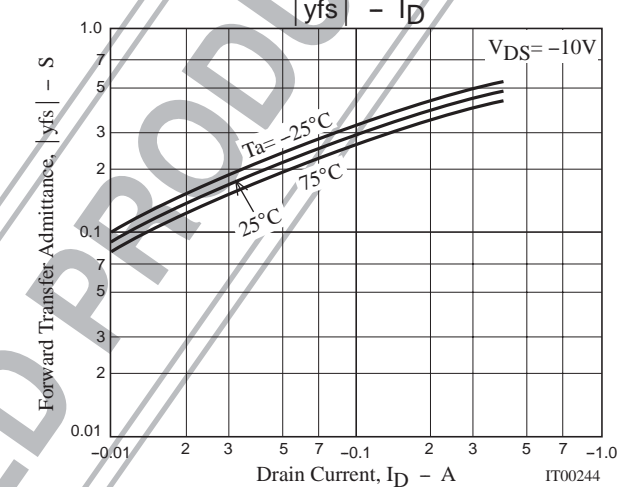
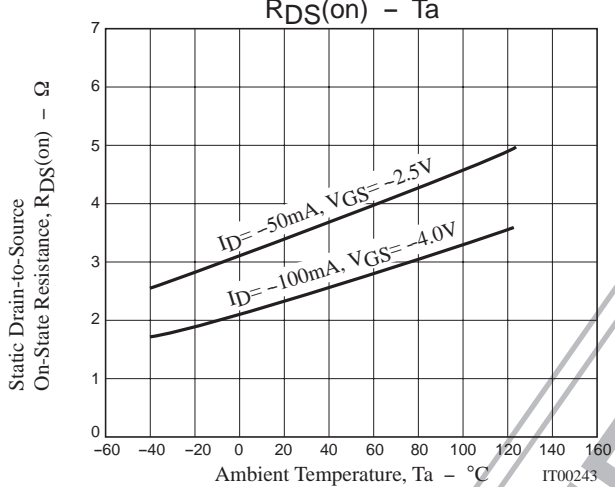
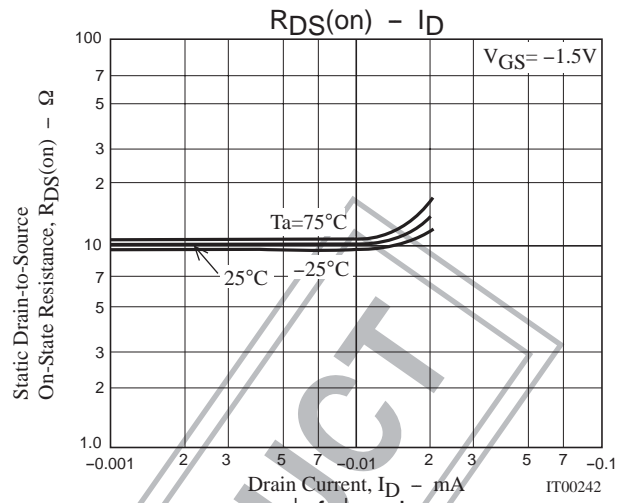
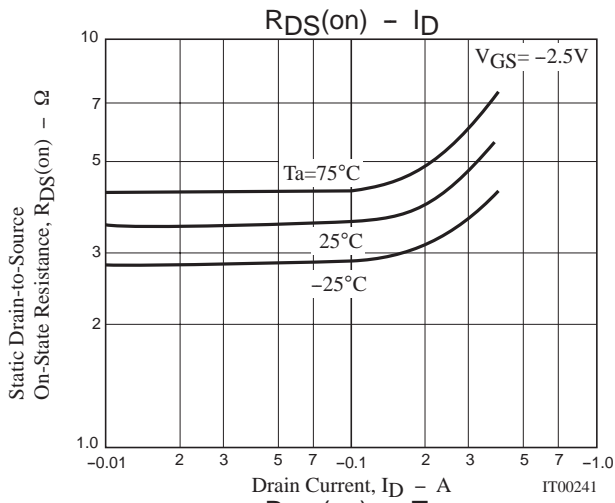
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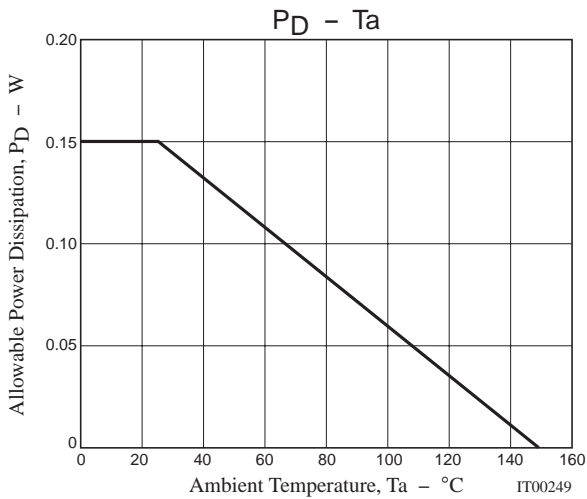
Switching Time Test Circuit



3LP02M



3LP02M



Note on usage : Since the 3LP02M is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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